

WHAT IS CLAIMED IS:

1. A method for manufacturing a semiconductor device, comprising the following steps of, upon processing a wafer having a supporting body and an intermediate insulating film provided over the whole upper surface of the supporting body to thereby fabricate the semiconductor device:

(a) removing a layered portion of the intermediate insulating film, which is provided on a wafer edge region lying around the wafer, by etching using a resist pattern to thereby expose an edge surface region of the supporting body, which corresponds to the wafer edge region; and

(b) forming a conductive layer by sputtering so as to cover said exposed edge surface region and the remaining intermediate insulating film from the upper side.

2. A method according to claim 1, wherein said resist pattern forming step includes, as steps prior to said step (a),

a step for forming a resist film over the entire upper surface of the intermediate insulating film,

a step for effecting a peripheral exposure on a resist edge region corresponding to the wafer edge region, of the resist film by using a peripheral exposure function of an exposure system, and

a step for removing the resist edge region subjected to the peripheral exposure.

3. A method according to claim 1, wherein said resist pattern forming step includes, as steps prior to said step (a),

a step for forming a resist film over the entire upper surface of the

intermediate insulating film, and

a step for applying chemicals onto the upper surface of the resist film by a spin coating apparatus to remove the resist edge region corresponding to the wafer edge region, of the resist film.

4. A method according to claim 1, wherein the supporting body is formed of a material selected from a semiconductor material and a conductive material.

5. A method according to claim 2, wherein the supporting body is formed of a material selected from a semiconductor material and a conductive material.

6. A method according to claim 3, wherein the supporting body is formed of a material selected from a semiconductor material and a conductive material.